



# MCH6601 — P-Channel Silicon MOSFET

## General-Purpose Switching Device Applications

### Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 1.5V drive.
- Composite type with 2 MOSFETs contained in a single package, facilitating high-density mounting.

### Specifications

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		-30	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±10	V
Drain Current (DC)	I <sub>D</sub>		-0.2	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	-0.8	A
Allowable Power Dissipation	P <sub>D</sub>	Mounted on a ceramic board (900mm <sup>2</sup> ×0.8mm) 1unit	0.8	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

#### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =-1mA, V <sub>GS</sub> =0V	-30			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V			-1	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-100μA	-0.4		-1.4	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-50mA	80	110		mS
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =-50mA, V <sub>GS</sub> =-4V		8	10.4	Ω
	R <sub>DS(on)2</sub>	I <sub>D</sub> =-30mA, V <sub>GS</sub> =-2.5V		11	15.4	Ω
	R <sub>DS(on)3</sub>	I <sub>D</sub> =-1mA, V <sub>GS</sub> =-1.5V		27	54	Ω
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-10V, f=1MHz		7.5		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =-10V, f=1MHz		5.7		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> =-10V, f=1MHz		1.8		pF

Marking : FA

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# MCH6601

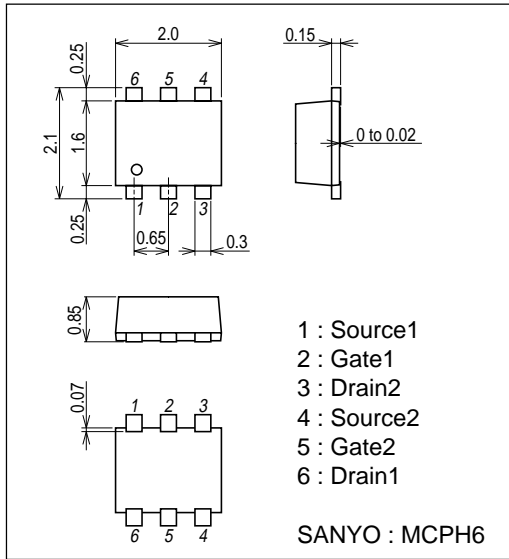
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Turn-ON Delay Time	$t_d(\text{on})$	See specified Test Circuit.		24		ns
Rise Time	$t_r$	See specified Test Circuit.		55		ns
Turn-OFF Delay Time	$t_d(\text{off})$	See specified Test Circuit.		120		ns
Fall Time	$t_f$	See specified Test Circuit.		130		ns
Total Gate Charge	$Q_g$	$V_{DS}=-10V, V_{GS}=-10V, I_D=-100mA$		1.43		nC
Gate-to-Source Charge	$Q_{gs}$	$V_{DS}=-10V, V_{GS}=-10V, I_D=-100mA$		0.18		nC
Gate-to-Drain "Miller" Charge	$Q_{gd}$	$V_{DS}=-10V, V_{GS}=-10V, I_D=-100mA$		0.25		nC
Diode Forward Voltage	$V_{SD}$	$I_S=-100mA, V_{GS}=0V$		-0.83	-1.2	V

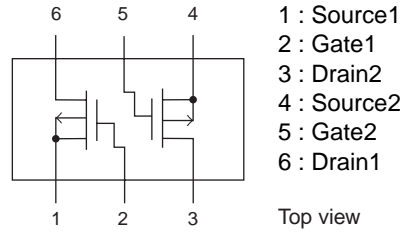
## Package Dimensions

unit : mm

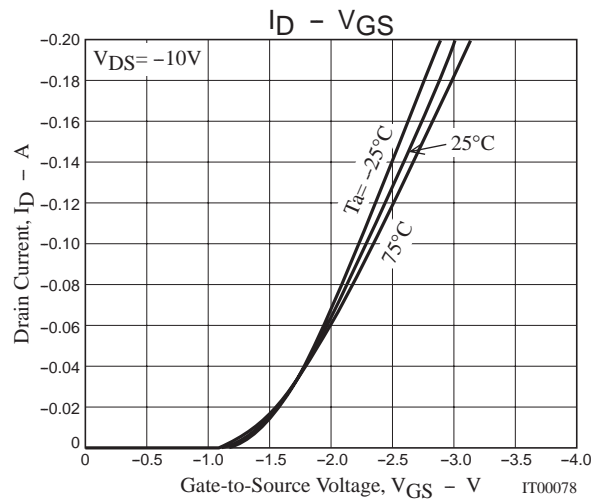
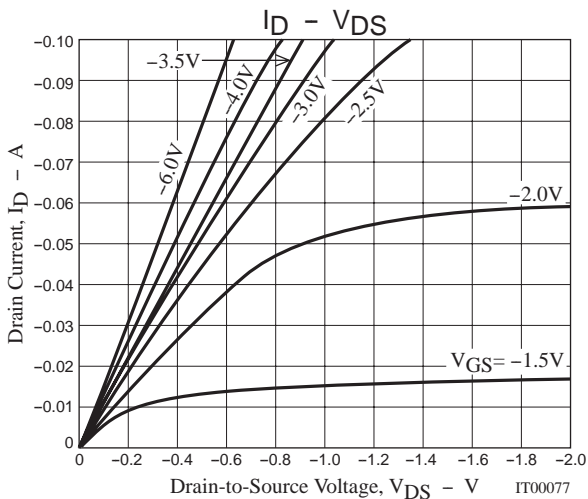
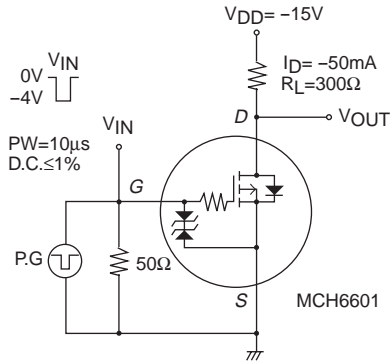
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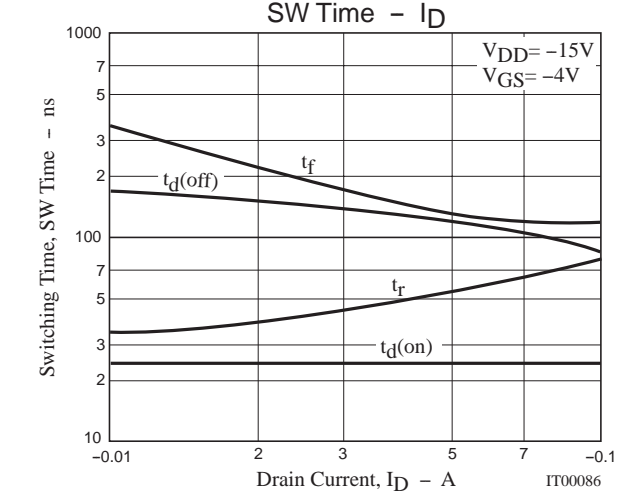
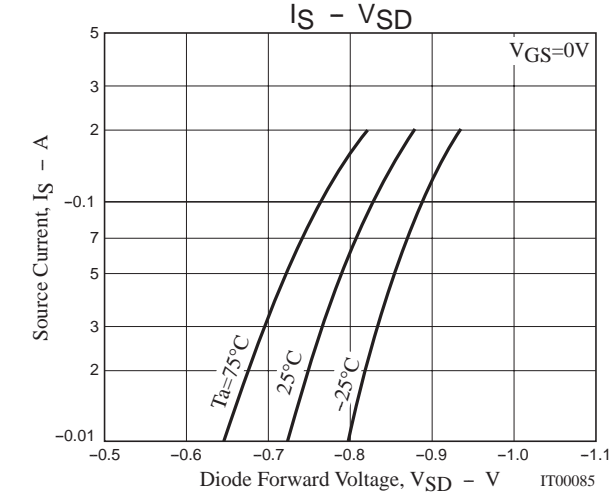
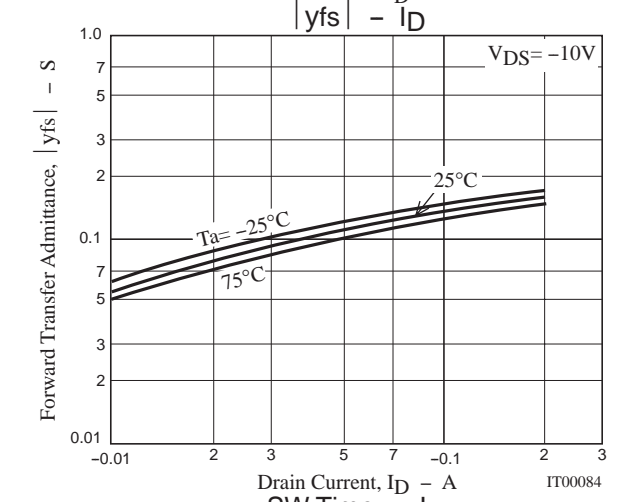
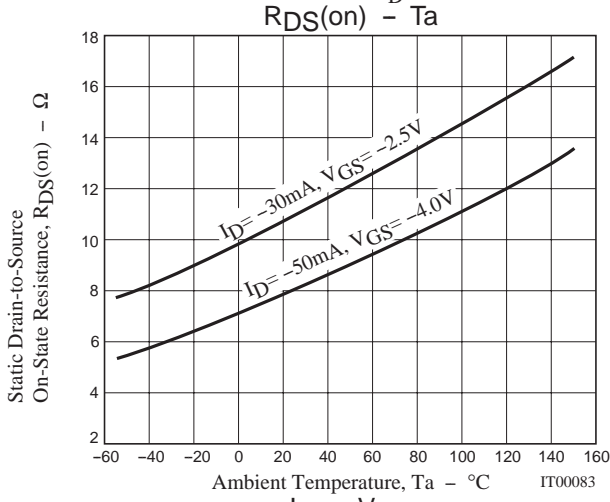
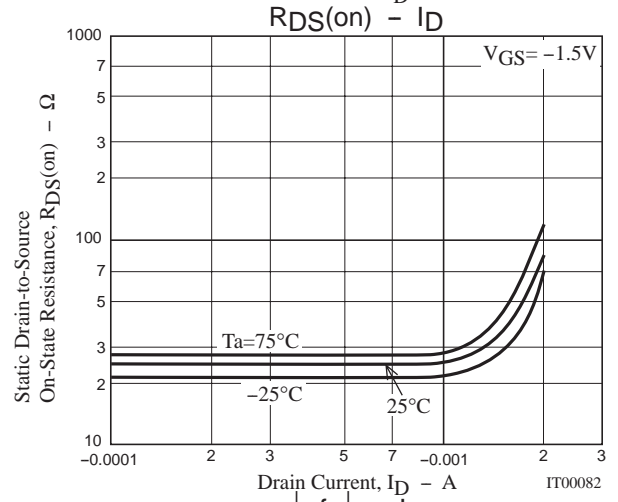
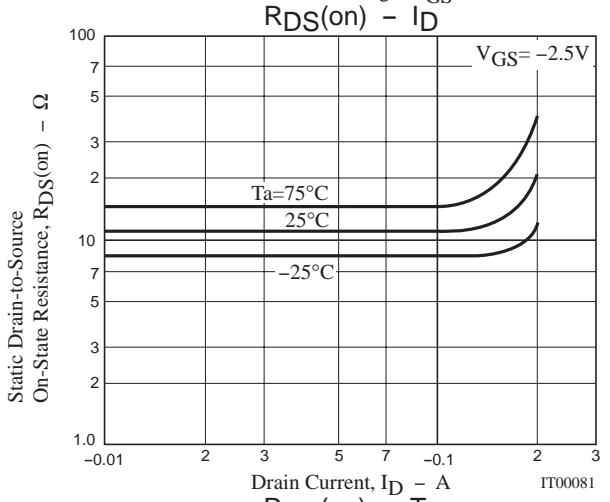
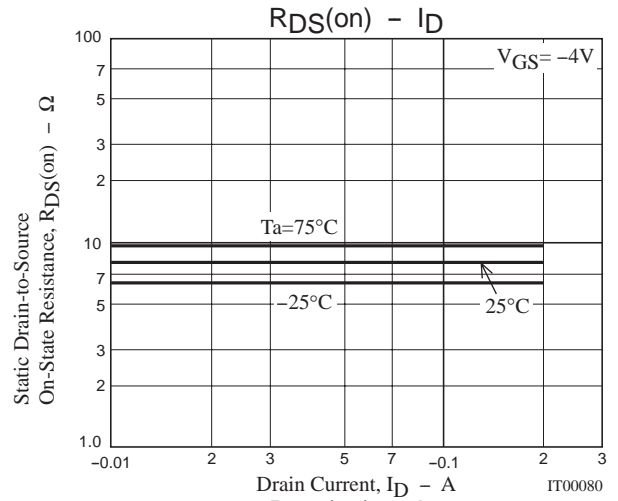
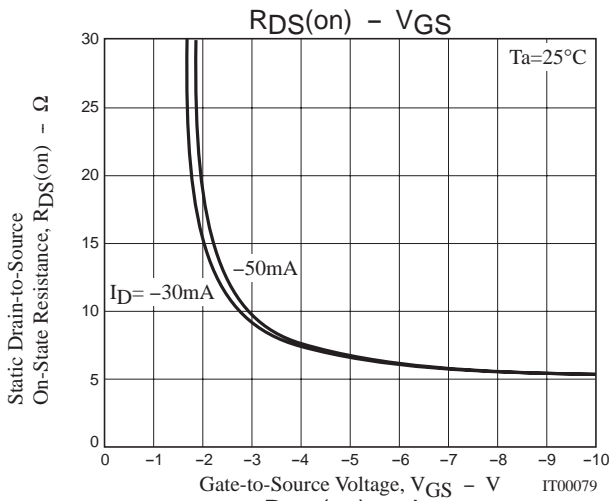
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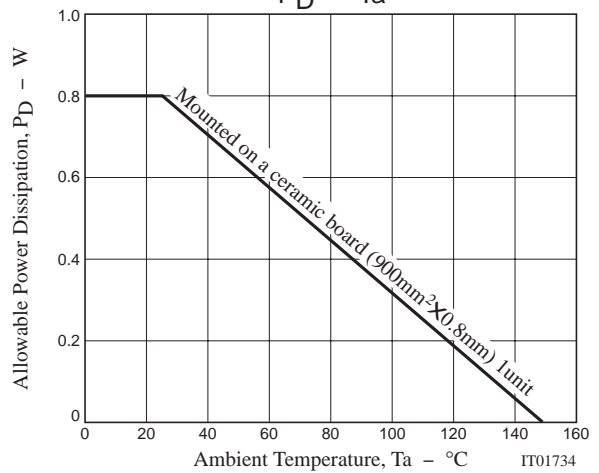
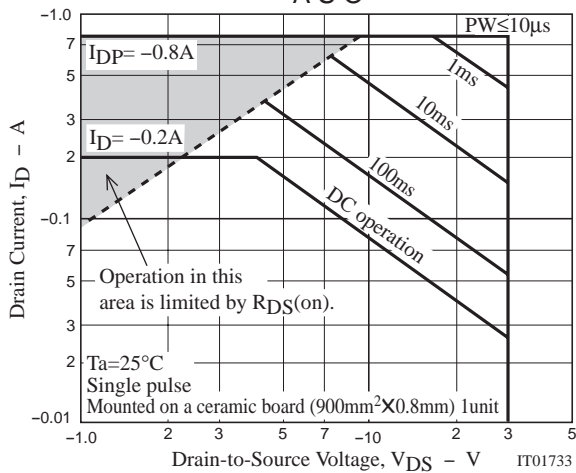
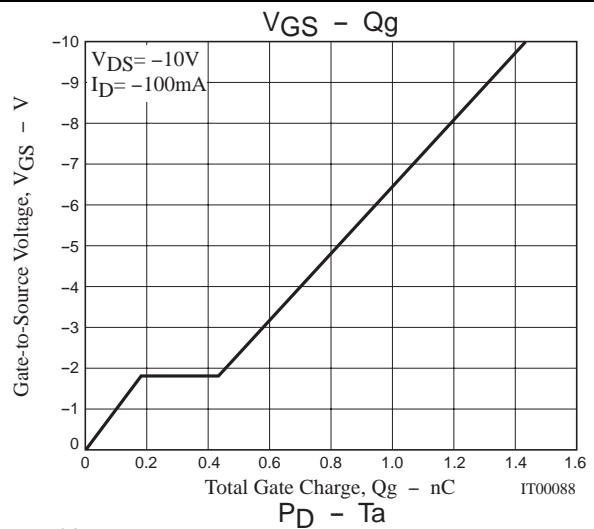
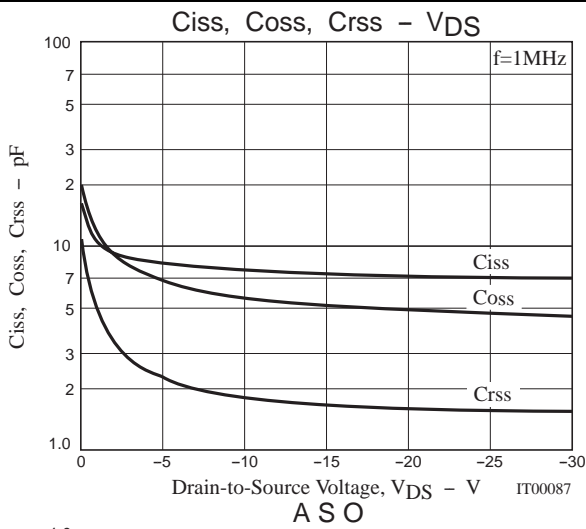


## Switching Time Test Circuit



# MCH6601





Note on usage : Since the MCH6601 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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